

L Number	Hits	Search Text	DB	Time stamp
34	2	((("6207522") or ("6218233")).PN.	USPAT; US-PGPUB	2004/08/08 17:52
35	2	((("6207522") or ("6218233")).PN.) and ("Same" common identical)	USPAT; US-PGPUB	2004/08/08 17:52
36	2	((("6207522") or ("6218233")).PN.) and ("Same" common identical)	USPAT; US-PGPUB	2004/08/08 17:54
37	1	((("6207522") or ("6218233")).PN.) and (chamber station)	USPAT; US-PGPUB	2004/08/08 18:00
39	1	((("6207522") or ("6218233")).PN.) and (pressure)	USPAT; US-PGPUB	2004/08/08 18:01
38	227	\$cvd same (("same" near2 (film layer material)) with ("same" near2 (chamber conditions pressure)))	USPAT; US-PGPUB	2004/08/08 18:16
40	0	\$cvd same (("same" near2 (film layer material)) with ("same" near2 (chamber conditions pressure)) with (but adj temperature))	USPAT; US-PGPUB	2004/08/08 18:16
-	1433	(CVD or (chemical adj vapor adj deposit\$)) with ((aluminum adj oxide) or "al.sub.2 o.sub.3")	USPAT; US-PGPUB	2004/08/04 18:53
-	280	((CVD or (chemical adj vapor adj deposit\$)) with ((aluminum adj oxide) or "al.sub.2 o.sub.3")) and (((aluminum adj oxide) or "al.sub.2 o.sub.3") with (two second) with (layer film))	USPAT; US-PGPUB	2004/08/04 18:53
-	1433	(CVD or (chemical adj vapor adj deposit\$)) with ((aluminum adj oxide) or "al.sub.2 o.sub.3")	USPAT; US-PGPUB	2004/08/05 08:23
-	280	((CVD or (chemical adj vapor adj deposit\$)) with ((aluminum adj oxide) or "al.sub.2 o.sub.3")) and (((aluminum adj oxide) or "al.sub.2 o.sub.3") with (two second) with (layer film))	USPAT; US-PGPUB	2004/08/04 18:54
-	8	((CVD or (chemical adj vapor adj deposit\$)) with ((aluminum adj oxide) or "al.sub.2 o.sub.3")) and (((aluminum adj oxide) or "al.sub.2 o.sub.3") with (two second) with (layer film))) and ((second different) adj temperature)	USPAT; US-PGPUB	2004/08/04 18:59
-	63	((CVD or (chemical adj vapor adj deposit\$)) with ((aluminum adj oxide) or "al.sub.2 o.sub.3")) and (((aluminum adj oxide) or "al.sub.2 o.sub.3") with (two second) with (layer film))) and (capacitor dram)	USPAT; US-PGPUB	2004/08/05 07:52
-	4240	(above higher lower below) near2 (oxidation near4 temperature)	USPAT; US-PGPUB	2004/08/05 08:23
-	432	((above higher lower below) near2 (oxidation near4 temperature)) and (capacitor dram)	USPAT; US-PGPUB	2004/08/05 13:46
-	131	((CVD or (chemical adj vapor adj deposit\$)) with ((aluminum adj oxide) or "al.sub.2 o.sub.3")) and (((aluminum adj oxide) or "al.sub.2 o.sub.3") with (two second) with (layer film))) and (capacitor dram)	USPAT; US-PGPUB	2004/08/05 07:52
-	425	((above higher lower below) near2 (oxidation near4 temperature)) and (capacitor dram) not (@ad>20030806 or @rlad>20030806)	USPAT; US-PGPUB	2004/08/05 07:53
-	126	((CVD or (chemical adj vapor adj deposit\$)) with ((aluminum adj oxide) or "al.sub.2 o.sub.3")) and (((aluminum adj oxide) or "al.sub.2 o.sub.3") with (two second) with (layer film))) and (capacitor dram)) not (@ad>20030806 or @rlad>20030806)	USPAT; US-PGPUB	2004/08/05 08:23

-	120	(((((above higher lower below) near2 (oxidation near4 temperature)) and (capacitor dram)) not (@ad>20030806 or @rlad>20030806)) and ((aluminum adj oxide) or "al.sub.2 o.sub.3"))	USPAT; US-PGPUB	2004/08/05 08:27
-	48	(((((above higher lower below) near2 (oxidation near4 temperature)) and (capacitor dram)) not (@ad>20030806 or @rlad>20030806)) and ((aluminum adj oxide) or "al.sub.2 o.sub.3"))) and (((tantalum titanium) adj nitride) "TiN" "TaN")	USPAT; US-PGPUB	2004/08/05 08:27
-	12	((above higher lower below) near2 (oxidation near4 temperature)) with (((tantalum titanium) adj nitride) "TiN" "TaN")	USPAT; US-PGPUB	2004/08/05 08:32
-	47	(((((above higher lower below) near2 (oxidation near4 temperature)) and (capacitor dram)) not (@ad>20030806 or @rlad>20030806)) and ((aluminum adj oxide) or "al.sub.2 o.sub.3"))) and (((tantalum titanium) adj nitride) "TiN" "TaN")) not (((above higher lower below) near2 (oxidation near4 temperature)) with (((tantalum titanium) adj nitride) "TiN" "TaN"))	USPAT; US-PGPUB	2004/08/05 08:33
-	46	((((((above higher lower below) near2 (oxidation near4 temperature)) and (capacitor dram)) not (@ad>20030806 or @rlad>20030806)) and ((aluminum adj oxide) or "al.sub.2 o.sub.3"))) and (((tantalum titanium) adj nitride) "TiN" "TaN")) not (((above higher lower below) near2 (oxidation near4 temperature)) with (((tantalum titanium) adj nitride) "TiN" "TaN"))) not (((CVD or (chemical adj vapor adj deposit\$)) with ((aluminum adj oxide) or "al.sub.2 o.sub.3"))) and (((aluminum adj oxide) or "al.sub.2 o.sub.3") with (two second) with (layer film))) and (capacitor dram)) not (@ad>20030806 or @rlad>20030806))	USPAT; US-PGPUB	2004/08/05 14:12
-	12929	(((((tantalum titanium) adj nitride) "TiN" "TaN") same (oxide with (CVD LPCVD HPCVD PECVD deposit depositing deposited deposition)))	USPAT; US-PGPUB	2004/08/05 14:08
-	2432	(((((tantalum titanium) adj nitride) "TiN" "TaN") same (oxide with (CVD LPCVD HPCVD PECVD deposit depositing deposited deposition))) and (oxide with oxidation)	USPAT; US-PGPUB	2004/08/05 14:11
-	1611	(((((tantalum titanium) adj nitride) "TiN" "TaN") same (oxide with (CVD LPCVD HPCVD PECVD deposit depositing deposited deposition))) and (oxide with oxidation)) and (438/\$.ccls. or 257/\$.ccls.)	USPAT; US-PGPUB	2004/08/05 15:21
-	1567	((((((tantalum titanium) adj nitride) "TiN" "TaN") same (oxide with (CVD LPCVD HPCVD PECVD deposit depositing deposited deposition))) and (oxide with oxidation)) and (438/\$.ccls. or 257/\$.ccls.)) not (@ad>20030806 or @rlad>20030806)	USPAT; US-PGPUB	2004/08/05 15:23
-	247	((((((tantalum titanium) adj nitride) "TiN" "TaN") same (oxide with (CVD LPCVD HPCVD PECVD deposit depositing deposited deposition))) and (oxide with oxidation)) and (438/\$.ccls. or 257/\$.ccls.)) not (@ad>20030806 or @rlad>20030806)) and ("al.sub.2 o.sub.3" (aluminum adj oxide))	USPAT; US-PGPUB	2004/08/05 14:52

-	982	(((((tantalum titanium) adj nitride) "TiN" "TaN") same (oxide with (CVD LPCVD HPCVD PECVD deposit depositing deposited deposition))) and (oxide with oxidation)) and (438/\$.ccls. or 257/\$.ccls.)) not (@ad>20030806 or @rlad>20030806)) and (capacitor dram)	USPAT; US-PGPUB	2004/08/06 11:52
-	314205	capacitor dram	USPAT; US-PGPUB	2004/08/05 15:12
-	3512	(capacitor dram) and ((second near2 (dielectric insulating insulator)) with ((higher above) temperature))	USPAT; US-PGPUB	2004/08/05 16:02
-	867	(capacitor dram) and ((aluminum adj oxide "al.sub 2 o.sub.3") with ((higher above) temperature))	USPAT; US-PGPUB	2004/08/05 16:01
-	3519	(capacitor dram) and ((second near2 (dielectric insulating insulator (aluminum adj oxide "al.sub 2 o.sub.3")) with ((higher above) temperature)))	USPAT; US-PGPUB	2004/08/05 15:54
-	329	((capacitor dram) and ((aluminum adj oxide "al.sub 2 o.sub.3") with ((higher above) temperature))) and (438/\$.ccls. or 257/\$.ccls.)	USPAT; US-PGPUB	2004/08/05 15:57
-	317	((capacitor dram) and ((aluminum adj oxide "al.sub 2 o.sub.3") with ((higher above) temperature))) and (438/\$.ccls. or 257/\$.ccls.)) not (@ad>20030806 or @rlad>20030806)	USPAT; US-PGPUB	2004/08/05 15:59
-	18428	(capacitor dram) and ((second near2 (dielectric insulating insulator (aluminum adj oxide "al.sub 2 o.sub.3")) with ((higher second above) temperature)))	USPAT; US-PGPUB	2004/08/05 15:54
-	18399	(capacitor dram) and ((second near2 (dielectric insulating insulator)) with ((higher second above) temperature))	USPAT; US-PGPUB	2004/08/06 11:49
-	183	((capacitor dram) and ((second near2 (dielectric insulating insulator)) with ((higher second above) temperature))) and ((aluminum adj oxide "al.sub 2 o.sub.3") with ((higher above) temperature))	USPAT; US-PGPUB	2004/08/05 15:59
-	339	((capacitor dram) and ((second near2 (dielectric insulating insulator)) with ((higher second above) temperature))) and ((aluminum adj oxide "al.sub 2 o.sub.3") with ((higher second above) temperature))	USPAT; US-PGPUB	2004/08/05 15:57
-	135	((capacitor dram) and ((second near2 (dielectric insulating insulator)) with ((higher second above) temperature))) and ((aluminum adj oxide "al.sub 2 o.sub.3") with ((higher above) temperature))) and (438/\$.ccls. or 257/\$.ccls.)	USPAT; US-PGPUB	2004/08/05 15:58
-	252	((capacitor dram) and ((second near2 (dielectric insulating insulator)) with ((higher second above) temperature))) and ((aluminum adj oxide "al.sub 2 o.sub.3") with ((higher second above) temperature))) and (438/\$.ccls. or 257/\$.ccls.)	USPAT; US-PGPUB	2004/08/05 15:58
-	127	((capacitor dram) and ((second near2 (dielectric insulating insulator)) with ((higher second above) temperature))) and ((aluminum adj oxide "al.sub 2 o.sub.3") with ((higher above) temperature))) and (438/\$.ccls. or 257/\$.ccls.)) not (@ad>20030806 or @rlad>20030806)	USPAT; US-PGPUB	2004/08/05 16:00

-	238	(((((capacitor dram) and ((second near2 (dielectric insulating insulator)) with ((higher second above) temperature))) and ((aluminum adj oxide "al.sub 2 o.sub.3") with ((higher second above) temperature))) and (438/\$.ccls. or 257/\$.ccls.)) not (@ad>20030806 or @rlad>20030806)	USPAT; US-PGPUB	2004/08/05 15:59
-	111	(((((capacitor dram) and ((second near2 (dielectric insulating insulator)) with ((higher second above) temperature))) and ((aluminum adj oxide "al.sub 2 o.sub.3") with ((higher second above) temperature))) and (438/\$.ccls. or 257/\$.ccls.)) not (@ad>20030806 or @rlad>20030806)) not (((((capacitor dram) and ((second near2 (dielectric insulating insulator)) with ((higher second above) temperature))) and ((aluminum adj oxide "al.sub 2 o.sub.3") with ((higher above) temperature))) and (438/\$.ccls. or 257/\$.ccls.)) not (@ad>20030806 or @rlad>20030806))	USPAT; US-PGPUB	2004/08/05 15:59
-	29	(((((capacitor dram) and ((second near2 (dielectric insulating insulator)) with ((higher second above) temperature))) and ((aluminum adj oxide "al.sub 2 o.sub.3") with ((higher above) temperature))) and (438/\$.ccls. or 257/\$.ccls.)) not (@ad>20030806 or @rlad>20030806)) and ((tantalum adj nitride) "Tan")	USPAT; US-PGPUB	2004/08/05 16:00
-	15	(capacitor dram) and ((aluminum adj oxide "al.sub 2 o.sub.3") with ((higher above) adj temperature))	USPAT; US-PGPUB	2004/08/05 16:03
-	9	(capacitor dram) and ((second near2 (dielectric insulating insulator)) with ((higher above) adj temperature))	USPAT; US-PGPUB	2004/08/05 16:03
-	17	(capacitor dram) and ((aluminum adj oxide "al.sub 2 o.sub.3") with ((higher second above) adj temperature))	USPAT; US-PGPUB	2004/08/05 16:06
-	49	((capacitor dram) and ((second near2 (dielectric insulating insulator)) with ((higher second above) adj temperature))) not ((capacitor dram) and ((aluminum adj oxide "al.sub 2 o.sub.3") with ((higher second above) adj temperature)))	USPAT; US-PGPUB	2004/08/05 16:07
-	49	(capacitor dram) and ((second near2 (dielectric insulating insulator)) with ((higher second above) adj temperature))	USPAT; US-PGPUB	2004/08/05 19:10
-	230	(jennifer near2 kennedy).xa	USPAT; US-PGPUB	2004/08/05 19:11
-	30	("5254505" "5256455" "5270241" "5392189" "5459635" "5470398" "5596214" "5614018" "5618761" "5656329" "5663089" "5719417" "5723361" "5731948" "5736759" "5776254" "5783253" "5798903" "5976990" "5989927" "6037205" "6043526" "6046345" "6078492" "6101085" "6153898" "6215650" "6258654" "6285051" "6287935").PN.	USPAT; US-PGPUB USPAT	2004/08/05 19:19 2004/08/05 19:19
-	1	("6207522").PN.	USPAT; US-PGPUB	2004/08/06 11:20
-	1	((("6207522").PN.) and silica	USPAT; US-PGPUB	2004/08/06 11:33
-	0	((("6207522").PN.) and (metal adj nitride)	USPAT; US-PGPUB	2004/08/06 11:33
-	1	((("6207522").PN.) and (nitride)	USPAT; US-PGPUB	2004/08/06 11:34
-	1	((("6207522").PN.) and (Tin tan)	USPAT; US-PGPUB	2004/08/06 11:37

-	1030648	thickness	USPAT; US-PGPUB	2004/08/06 11:37
-	1	((("6207522").PN.) and thickness	USPAT; US-PGPUB	2004/08/06 11:47
-	172268	438/\$.ccls. or 257/\$.ccls.	USPAT; US-PGPUB	2004/08/06 11:50
-	228	(438/\$.ccls. or 257/\$.ccls.) and ((prevent\$ near2 oxidat\$) with ("Tin" "tan" ((titanium tantalum) adj nitride)))	USPAT; US-PGPUB	2004/08/06 11:52
-	237	(438/\$.ccls. or 257/\$.ccls.) and ((prevent\$ near2 oxidat\$) with ("Tin" "tan" ((titanium tantalum metal) adj nitride)))	USPAT; US-PGPUB	2004/08/06 11:52
-	982	(((((tantalum titanium) adj nitride) "TiN" "TaN") same (oxide with (CVD LPCVD HPCVD PECVD deposit depositing deposited deposition))) and (oxide with oxidation)) and (438/\$.ccls. or 257/\$.ccls.)) not (@ad>20030806 or @rlad>20030806)) and (capacitor dram)	USPAT; US-PGPUB	2004/08/06 11:53
-	23	((438/\$.ccls. or 257/\$.ccls.) and ((prevent\$ near2 oxidat\$) with ("Tin" "tan" ((titanium tantalum metal) adj nitride)))) and ((((((tantalum titanium) adj nitride) "TiN" "TaN") same (oxide with (CVD LPCVD HPCVD PECVD deposit depositing deposited deposition))) and (oxide with oxidation)) and (438/\$.ccls. or 257/\$.ccls.)) not (@ad>20030806 or @rlad>20030806)) and (capacitor dram))	USPAT; US-PGPUB	2004/08/06 13:29
-	1	("6444478").PN.	USPAT; US-PGPUB	2004/08/06 13:29
-	1	((("6444478").PN.) and temperature	USPAT; US-PGPUB	2004/08/06 13:30
-	1	((("6444478").PN.) and temperature	USPAT; US-PGPUB	2004/08/06 13:30